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# PHPT61003PY

100 V, 3A PNP high power bipolar transistor

13 January 2014

Product data sheet

## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61003NY

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
$I_C$	collector current		-	-	-3	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse	-	-	-8	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -2$ A; $I_B = -200$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	110	180	m $\Omega$



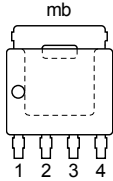
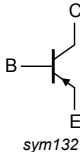
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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LPAK56; Power-SO8 (SOT669)</p>	 <p>sym132</p>
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61003PY	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61003PY	1003PAB

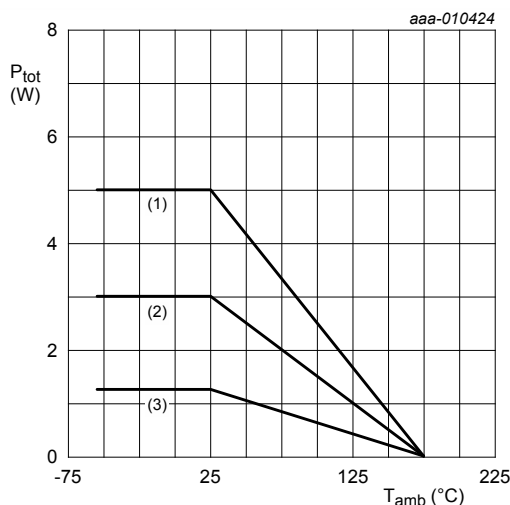
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{CBO}$	collector-base voltage	open emitter	-	-100	V	
$V_{CEO}$	collector-emitter voltage	open base	-	-100	V	
$V_{EBO}$	emitter-base voltage	open collector	-	-8	V	
$I_C$	collector current		-	-3	A	
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse	-	-8	A	
$I_B$	base current		-	-0.5	A	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
$T_j$	junction temperature		-	175	°C	
$T_{amb}$	ambient temperature		-55	175	°C	
$T_{stg}$	storage temperature		-65	175	°C	

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

**Fig. 1. Power derating curves**

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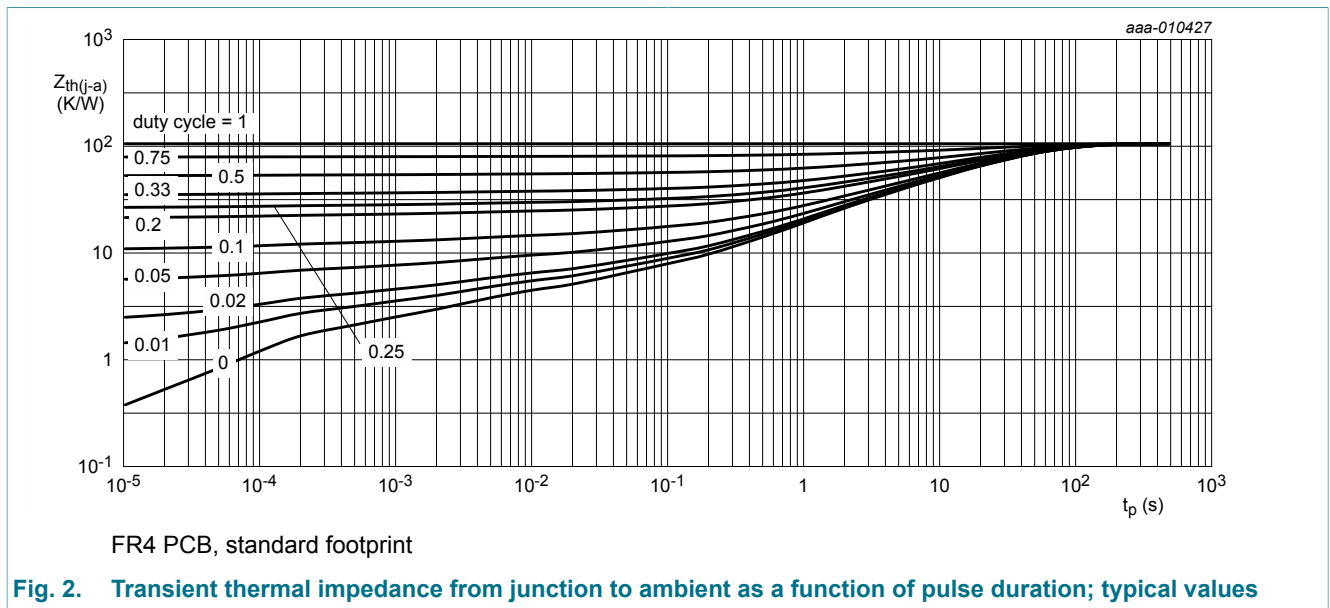
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**9. Thermal characteristics**

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	6	K/W

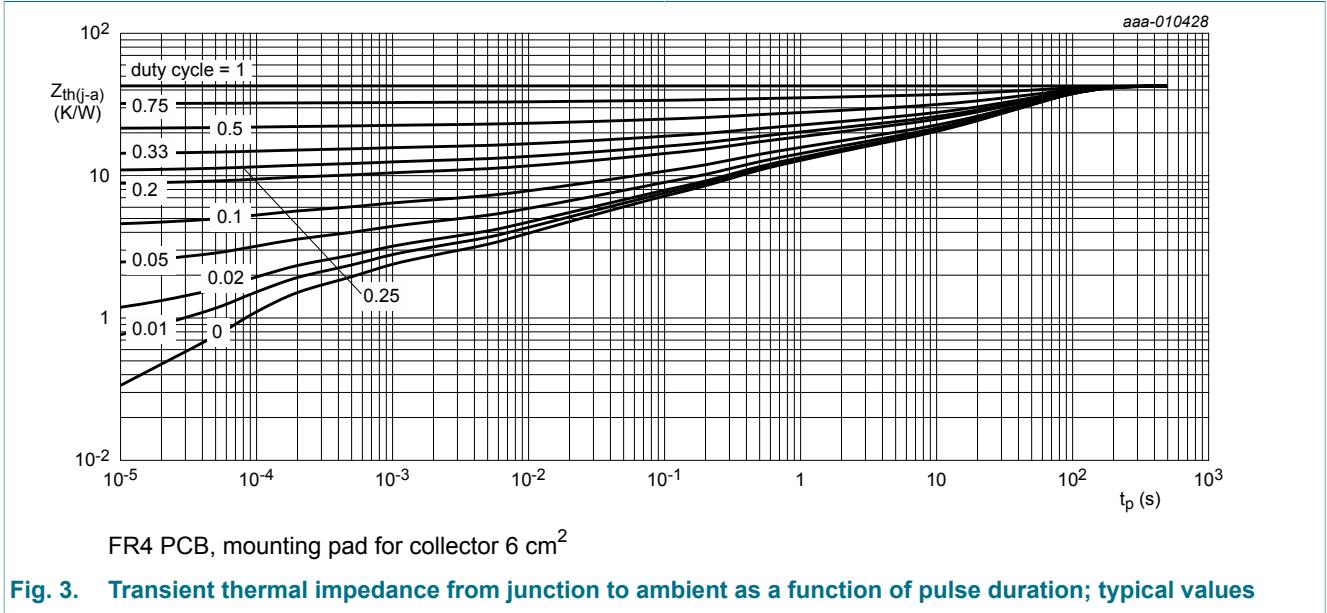
- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic PCB; Al<sub>2</sub>O<sub>3</sub>; standard footprint.



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## 10. Characteristics

**Table 7. Characteristics**

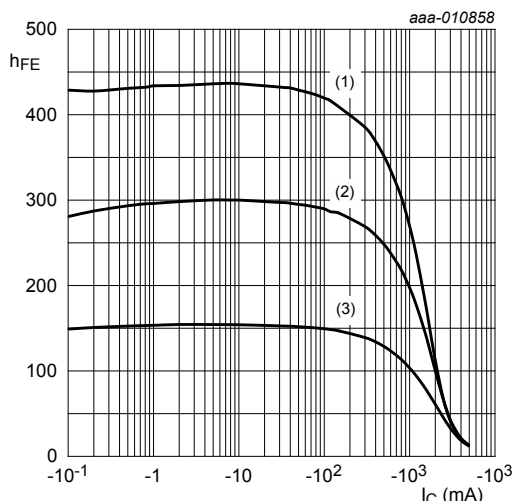
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	150	220	-	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	80	210	-	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -2 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	20	100	-	
		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -3 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	10	40	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-70	-110	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-220	-360	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	110	180	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-0.91	-1	V
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-1.02	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-0.68	-0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -1 A; I <sub>Bon</sub> = -50 mA; I <sub>Boff</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	20	-	ns
t <sub>r</sub>	rise time		-	180	-	ns
t <sub>on</sub>	turn-on time		-	200	-	ns
t <sub>s</sub>	storage time		-	350	-	ns
t <sub>f</sub>	fall time		-	220	-	ns
t <sub>off</sub>	turn-off time		-	570	-	ns
f <sub>T</sub>	transition frequency		V <sub>CE</sub> = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	125	-

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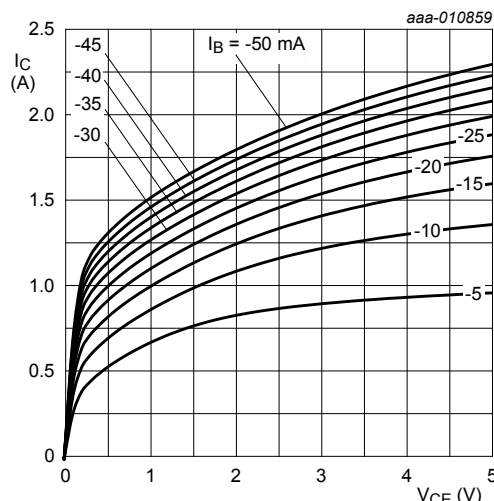
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	30	-	pF



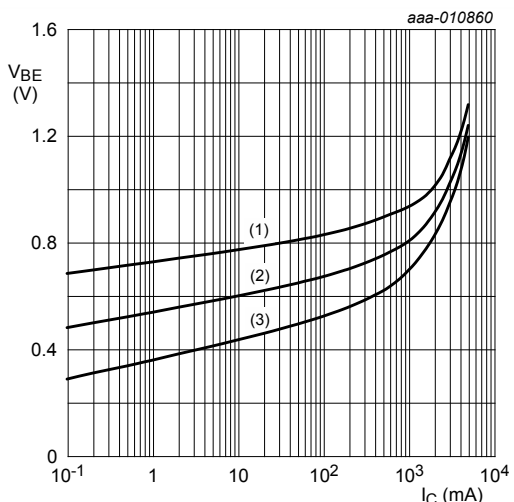
$V_{CE} = -10\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 4. DC current gain as a function of collector current; typical values**



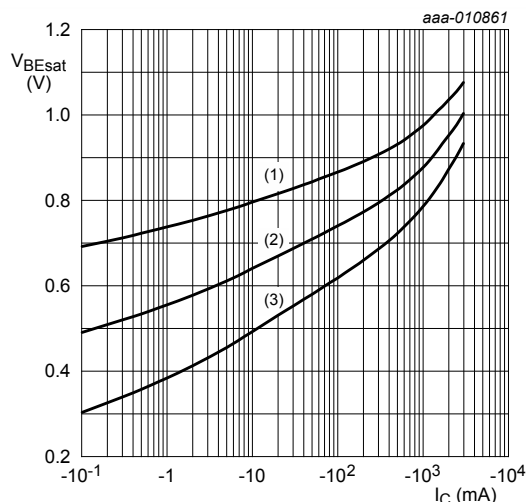
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 5. Collector current as a function of collector-emitter voltage; typical values**



$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig. 6. Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

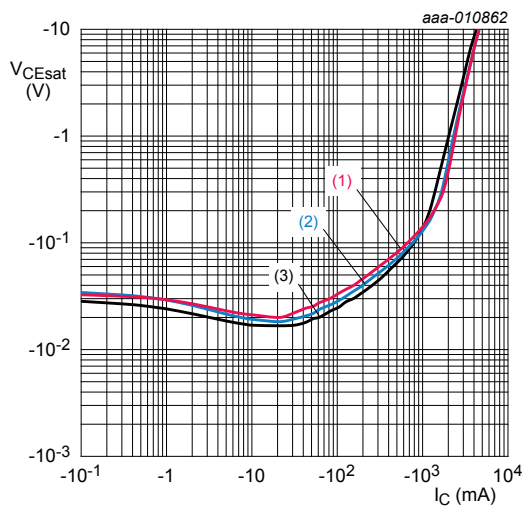
**Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values**



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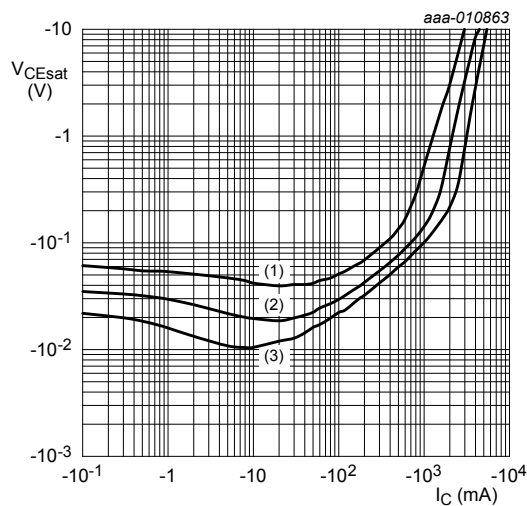
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100 V, 3A PNP high power bipolar transistor



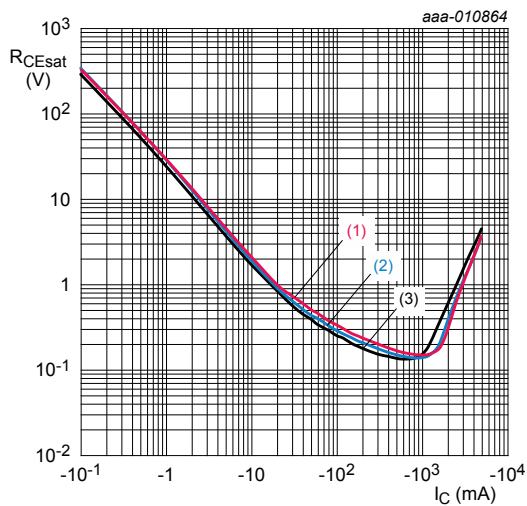
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values**



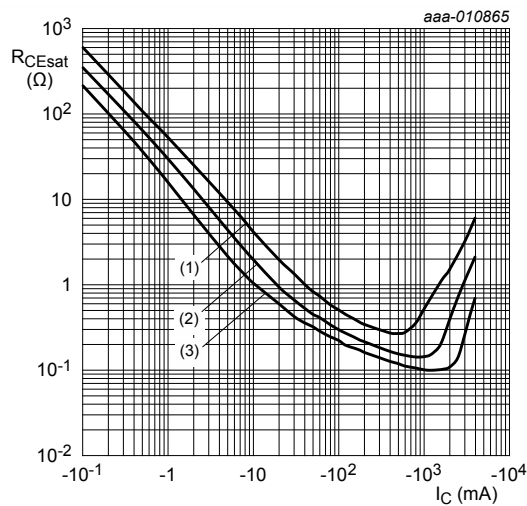
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 50$   
 (2)  $I_C/I_B = 20$   
 (3)  $I_C/I_B = 10$

**Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 50$   
 (2)  $I_C/I_B = 20$   
 (3)  $I_C/I_B = 10$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**

## 11. Test information

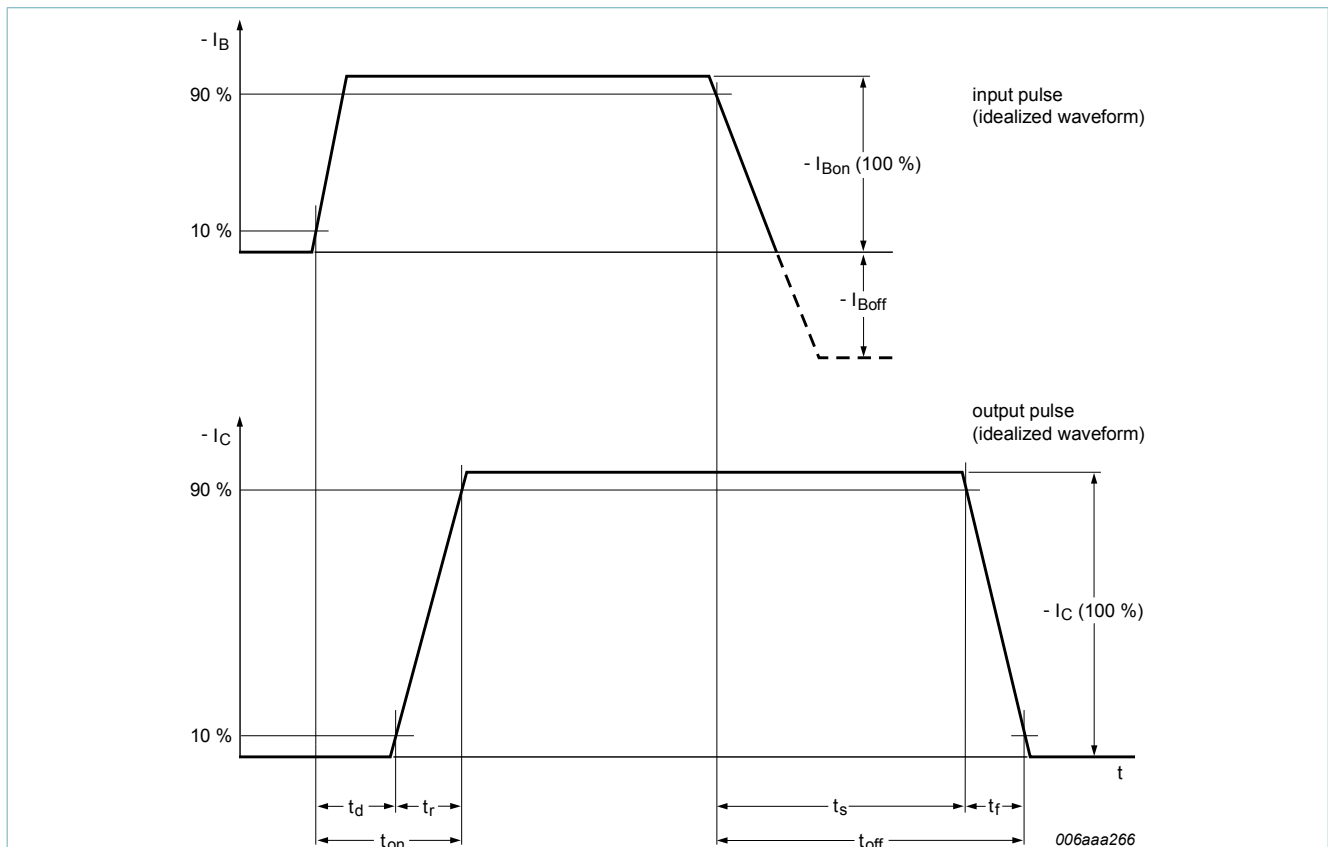


Fig. 12. BISS transistor switching time definition

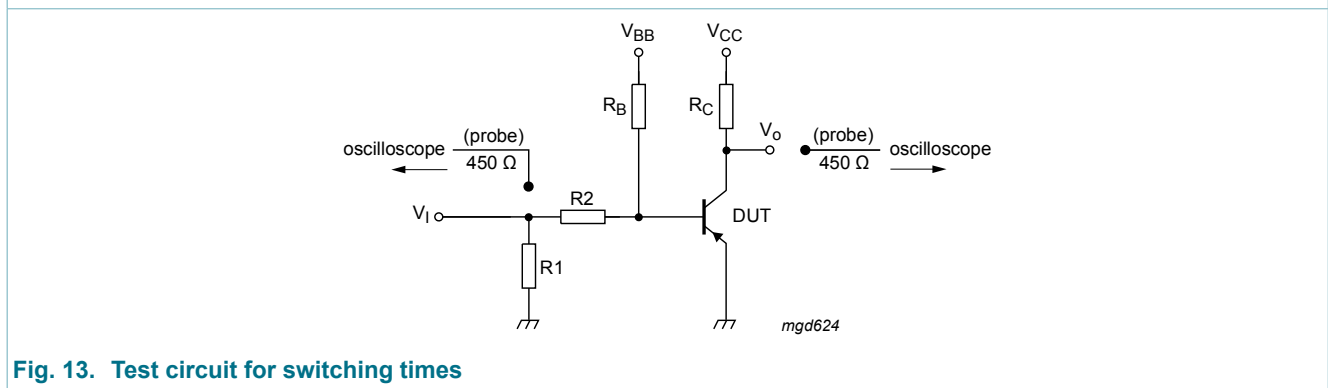


Fig. 13. Test circuit for switching times

### 11.1 Quality information

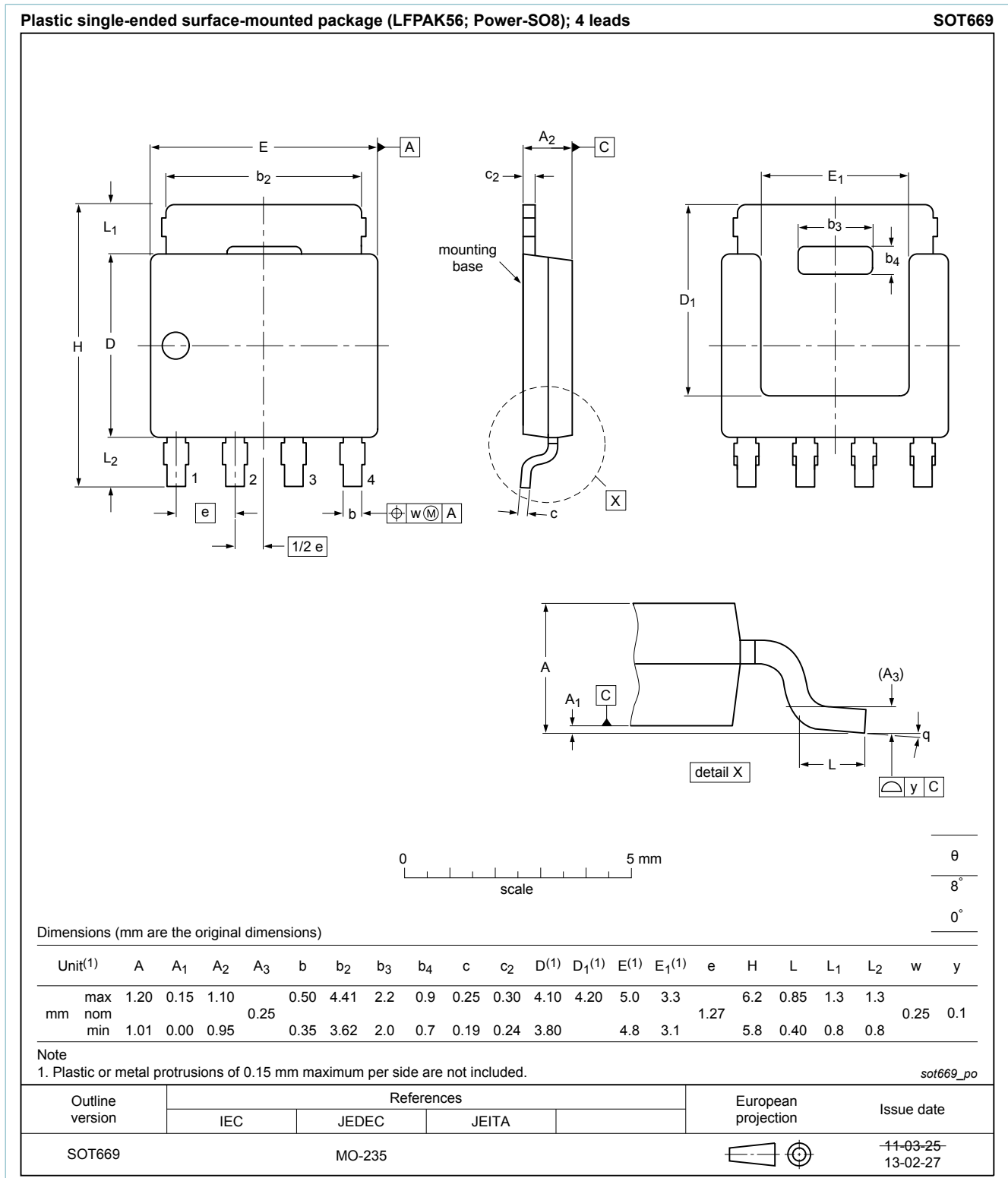
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**12. Package outline**



**Fig. 14. Package outline LPAK56; Power-SO8 (SOT669)**

13. Soldering

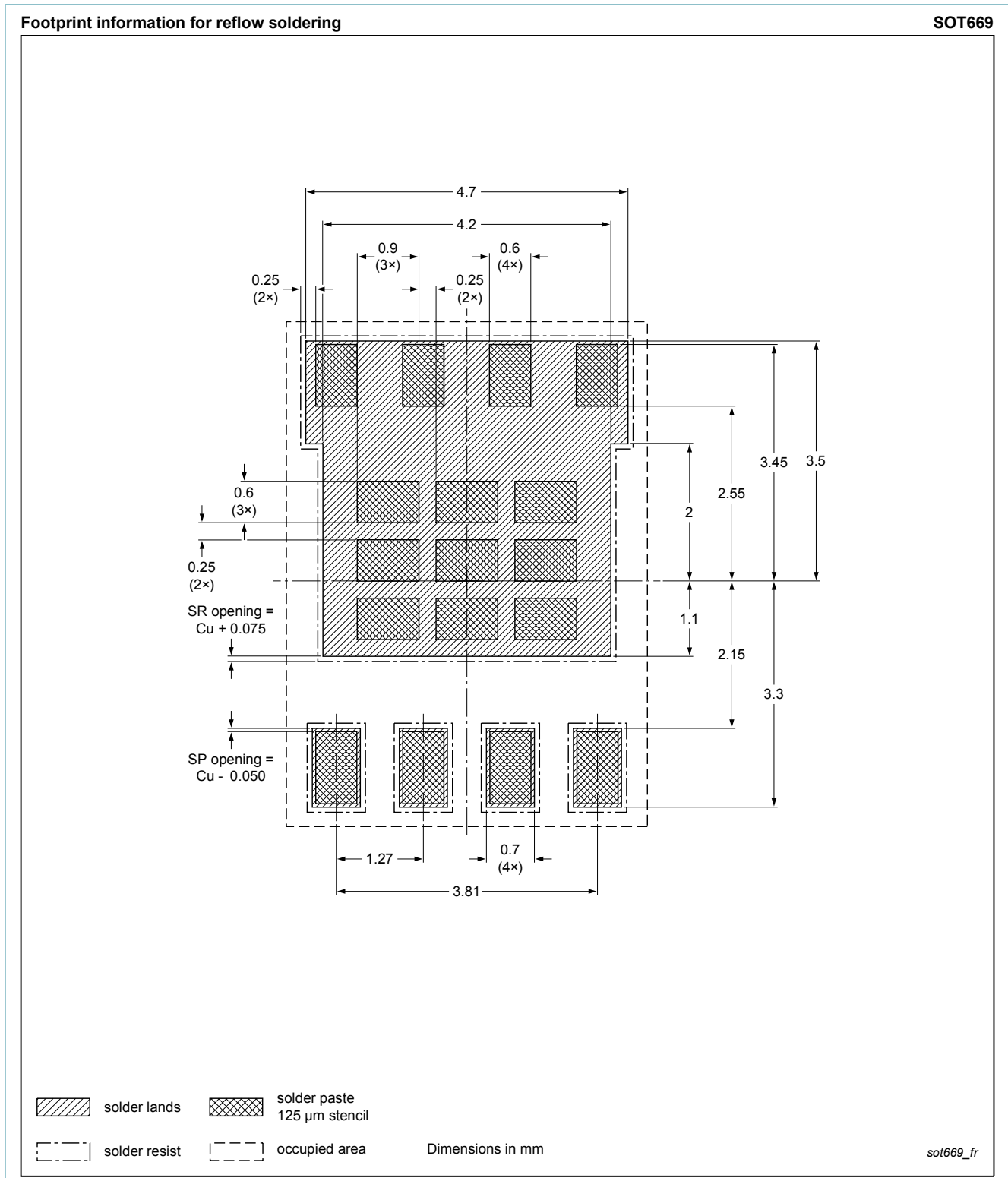


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

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## 14. Revision history

**Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003PY v.1	20140113	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 16. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	3
9	Thermal characteristics .....	4
10	Characteristics .....	6
11	Test information .....	9
11.1	Quality information .....	9
12	Package outline .....	10
13	Soldering .....	11
14	Revision history .....	12
15	Legal information .....	13
15.1	Data sheet status .....	13
15.2	Definitions .....	13
15.3	Disclaimers .....	13
15.4	Trademarks .....	14

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